

# STF30NM50N-VB Datasheet

## N-Channel 500-V (D-S) Super Junction MOSFET

| PRODUCT SUMMARY                    |                 |       |
|------------------------------------|-----------------|-------|
| $V_{DS}$ (V) at $T_J$ max.         | 500             |       |
| $R_{DS(on)}$ at 25 °C ( $\Omega$ ) | $V_{GS} = 10$ V | 0.115 |
| $Q_g$ (Max.) (nC)                  | 86              |       |
| $Q_{gs}$ (nC)                      | 14              |       |
| $Q_{gd}$ (nC)                      | 25              |       |
| Configuration                      | Single          |       |

### FEATURES

- Low figure-of-merit (FOM):  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)

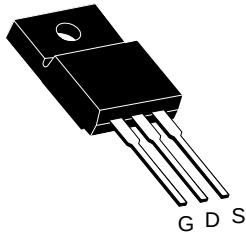


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

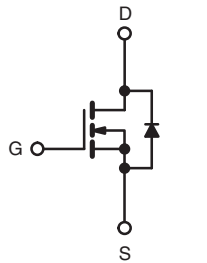
### APPLICATIONS

- Hard switched topologies
- Power factor correction power supplies (PFC)
- Switch mode power supplies (SMPS)
- Computing
  - PC silver box / ATX power supplies
- Lighting
  - Two stage LED lighting

TO-220 FULLPAK



Top View



N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted) |                                               |                         |                                   |             |      |
|---------------------------------------------------------------------------|-----------------------------------------------|-------------------------|-----------------------------------|-------------|------|
| PARAMETER                                                                 |                                               |                         | SYMBOL                            | LIMIT       | UNIT |
| Drain-Source Voltage                                                      |                                               |                         | V <sub>DS</sub>                   | 500         | V    |
| Gate-Source Voltage                                                       |                                               |                         | V <sub>GS</sub>                   | ± 30        |      |
| Continuous Drain Current (T <sub>J</sub> = 150 °C)                        | V <sub>GS</sub> at 10 V                       | T <sub>C</sub> = 25 °C  | I <sub>D</sub>                    | 30          | A    |
|                                                                           |                                               | T <sub>C</sub> = 100 °C |                                   | 18          |      |
| Pulsed Drain Current <sup>a</sup>                                         |                                               |                         | I <sub>DM</sub>                   | 105         |      |
| Linear Derating Factor                                                    |                                               |                         |                                   | 0.2         | W/°C |
| Single Pulse Avalanche Energy <sup>b</sup>                                |                                               |                         | E <sub>AS</sub>                   | 273         | mJ   |
| Maximum Power Dissipation                                                 |                                               |                         | P <sub>D</sub>                    | 80          | W    |
| Operating Junction and Storage Temperature Range                          |                                               |                         | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150 | °C   |
| Drain-Source Voltage Slope                                                | V <sub>DS</sub> = 0 V to 80 % V <sub>DS</sub> |                         | dV/dt                             | 65          | V/ns |
| Reverse Diode dV/dt <sup>d</sup>                                          |                                               | 25                      |                                   |             |      |
| Soldering Recommendations (Peak Temperature) <sup>c</sup>                 | for 10 s                                      |                         |                                   | 300         | °C   |

#### Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature.  
 b.  $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 4.4$  A.  
 c. 1.6 mm from case.  
 d.  $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C.

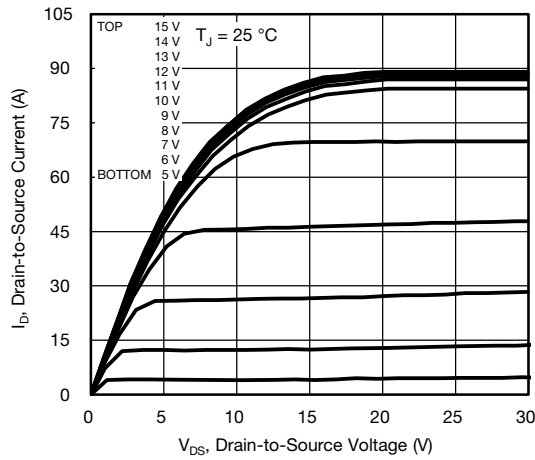
| THERMAL RESISTANCE RATINGS       |            |      |      |      |
|----------------------------------|------------|------|------|------|
| PARAMETER                        | SYMBOL     | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient      | $R_{thJA}$ | -    | 65   | °C/W |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | -    | 3.2  |      |

| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted) |                                  |                                                                                                      |                                                                                       |      |       |       |      |
|-----------------------------------------------------------------|----------------------------------|------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|------|-------|-------|------|
| PARAMETER                                                       | SYMBOL                           | TEST CONDITIONS                                                                                      |                                                                                       | MIN. | TYP.  | MAX.  | UNIT |
| Static                                                          |                                  |                                                                                                      |                                                                                       |      |       |       |      |
| Drain-Source Breakdown Voltage                                  | V <sub>DS</sub>                  | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                       |                                                                                       | 500  | -     | -     | V    |
| V <sub>DS</sub> Temperature Coefficient                         | ΔV <sub>DS</sub> /T <sub>J</sub> | Reference to 25 °C, I <sub>D</sub> = 1 mA                                                            |                                                                                       | -    | 0.59  | -     | V/°C |
| Gate-Source Threshold Voltage (N)                               | V <sub>GS(th)</sub>              | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                          |                                                                                       | 2.0  | -     | 4.0   | V    |
| Gate-Source Leakage                                             | I <sub>GSS</sub>                 | V <sub>GS</sub> = ± 20 V                                                                             |                                                                                       | -    | -     | ± 100 | nA   |
|                                                                 |                                  | V <sub>GS</sub> = ± 30 V                                                                             |                                                                                       | -    | -     | ± 1   | μA   |
| Zero Gate Voltage Drain Current                                 | I <sub>DSS</sub>                 | V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V                                                       |                                                                                       | -    | -     | 1     | μA   |
|                                                                 |                                  | V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C                              |                                                                                       | -    | -     | 25    |      |
| Drain-Source On-State Resistance                                | R <sub>DS(on)</sub>              | V <sub>GS</sub> = 10 V                                                                               | I <sub>D</sub> = 12 A                                                                 | -    | 0.115 | -     | Ω    |
| Forward Transconductance                                        | g <sub>fs</sub>                  | V <sub>DS</sub> = 30 V, I <sub>D</sub> = 12 A                                                        |                                                                                       | -    | 6.6   | -     | S    |
| Dynamic                                                         |                                  |                                                                                                      |                                                                                       |      |       |       |      |
| Input Capacitance                                               | C <sub>iss</sub>                 | V <sub>GS</sub> = 0 V,<br>V <sub>DS</sub> = 100 V,<br>f = 1 MHz                                      |                                                                                       | -    | 1980  | -     | pF   |
| Output Capacitance                                              | C <sub>oss</sub>                 |                                                                                                      |                                                                                       | -    | 105   | -     |      |
| Reverse Transfer Capacitance                                    | C <sub>rss</sub>                 |                                                                                                      |                                                                                       | -    | 8     | -     |      |
| Effective Output Capacitance, Energy Related <sup>a</sup>       | C <sub>o(er)</sub>               | V <sub>DS</sub> = 0 V to 400 V, V <sub>GS</sub> = 0 V                                                |                                                                                       | -    | 105   | -     |      |
| Effective Output Capacitance, Time Related <sup>b</sup>         | C <sub>o(tr)</sub>               |                                                                                                      |                                                                                       | -    | 285   | -     |      |
| Total Gate Charge                                               | Q <sub>g</sub>                   | V <sub>GS</sub> = 10 V                                                                               | I <sub>D</sub> = 12 A, V <sub>DS</sub> = 400 V                                        | -    | 57    | 86    | nC   |
| Gate-Source Charge                                              | Q <sub>gs</sub>                  |                                                                                                      |                                                                                       | -    | 14    | -     |      |
| Gate-Drain Charge                                               | Q <sub>gd</sub>                  |                                                                                                      |                                                                                       | -    | 25    | -     |      |
| Turn-On Delay Time                                              | t <sub>d(on)</sub>               | V <sub>DD</sub> = 400 V, I <sub>D</sub> = 12 A<br>R <sub>g</sub> = 9.1 Ω, V <sub>GS</sub> = 10 V     |                                                                                       | -    | 19    | 38    | ns   |
| Rise Time                                                       | t <sub>r</sub>                   |                                                                                                      |                                                                                       | -    | 36    | 72    |      |
| Turn-Off Delay Time                                             | t <sub>d(off)</sub>              |                                                                                                      |                                                                                       | -    | 57    | 86    |      |
| Fall Time                                                       | t <sub>f</sub>                   |                                                                                                      |                                                                                       | -    | 29    | 58    |      |
| Gate Input Resistance                                           | R <sub>g</sub>                   | f = 1 MHz, open drain                                                                                |                                                                                       | -    | 0.56  | -     | Ω    |
| Drain-Source Body Diode Characteristics                         |                                  |                                                                                                      |                                                                                       |      |       |       |      |
| Continuous Source-Drain Diode Current                           | I <sub>S</sub>                   | MOSFET symbol showing the integral reverse p - n junction diode                                      |  | -    | -     | 12    | A    |
| Pulsed Diode Forward Current                                    | I <sub>SM</sub>                  |                                                                                                      |                                                                                       | -    | -     | 50    |      |
| Diode Forward Voltage                                           | V <sub>SD</sub>                  | T <sub>J</sub> = 25 °C, I <sub>S</sub> = 16.5 A, V <sub>GS</sub> = 0 V                               |                                                                                       | -    | -     | 1.2   | V    |
| Reverse Recovery Time                                           | t <sub>rr</sub>                  | T <sub>J</sub> = 25 °C, I <sub>F</sub> = I <sub>S</sub> ,<br>dI/dt = 100 A/μs, V <sub>R</sub> = 25 V |                                                                                       | -    | 338   | -     | ns   |
| Reverse Recovery Charge                                         | Q <sub>rr</sub>                  |                                                                                                      |                                                                                       | -    | 5.3   | -     | μC   |
| Reverse Recovery Current                                        | I <sub>RRM</sub>                 |                                                                                                      |                                                                                       | -    | 29    | -     | A    |

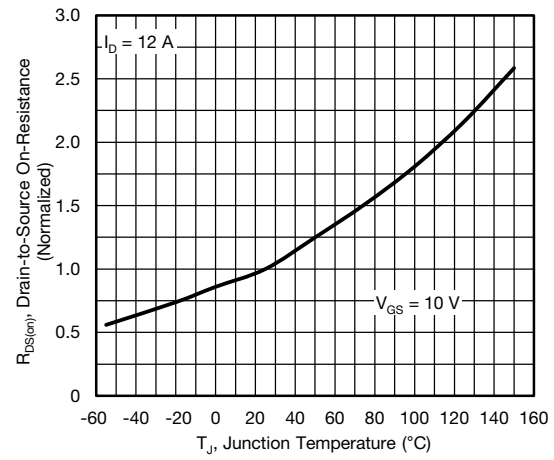
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .  
 b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

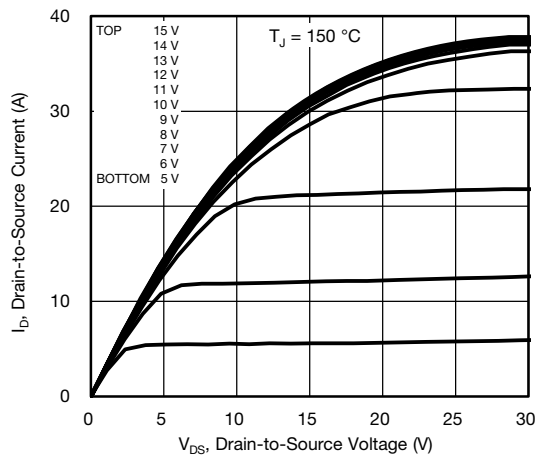
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



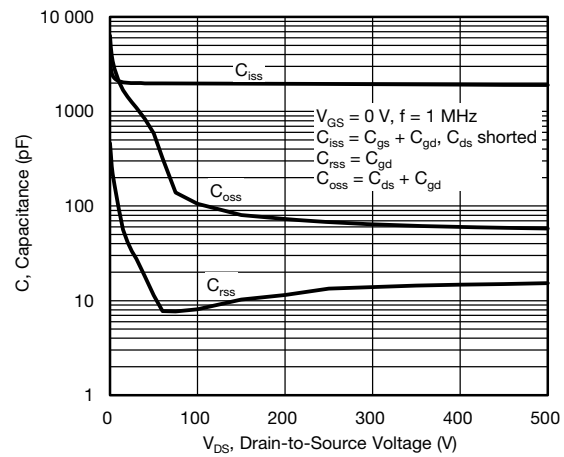
**Fig. 1 - Typical Output Characteristics**



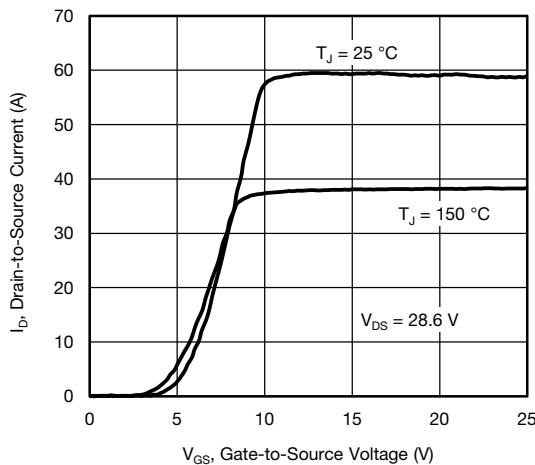
**Fig. 4 - Normalized On-Resistance vs. Temperature**



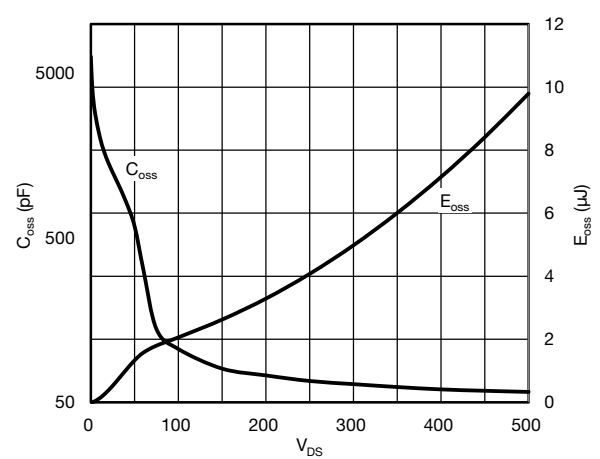
**Fig. 2 - Typical Output Characteristics**



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 6 -  $C_{oss}$  and  $E_{oss}$  vs.  $V_{DS}$**

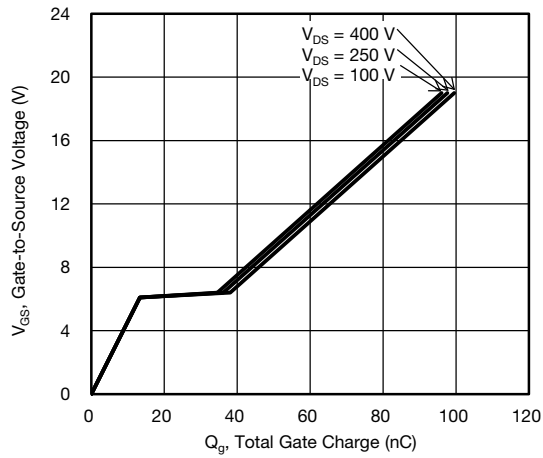


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

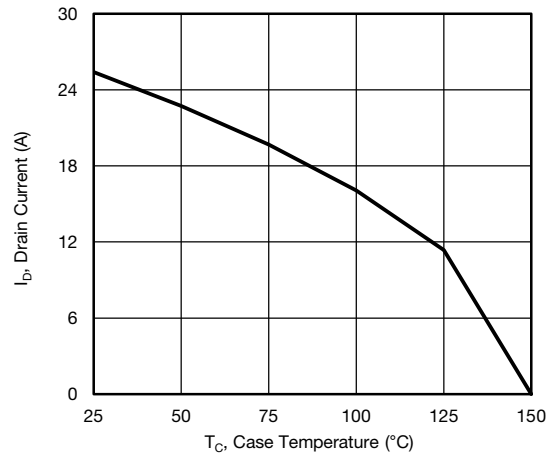


Fig. 10 - Maximum Drain Current vs. Case Temperature

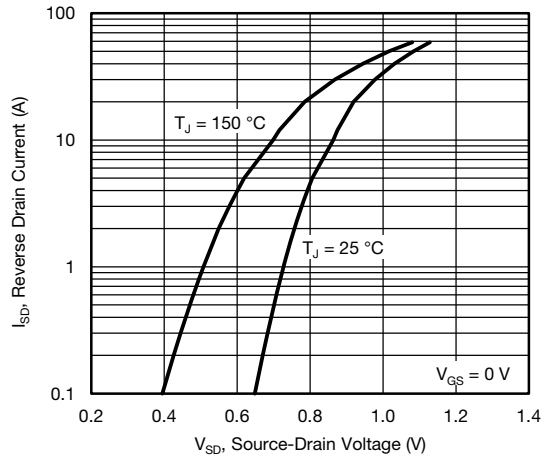


Fig. 8 - Typical Source-Drain Diode Forward Voltage

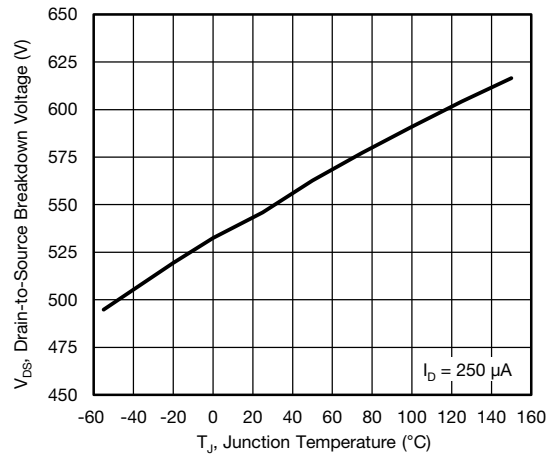


Fig. 11 - Typical Drain-to-Source Voltage vs. Temperature

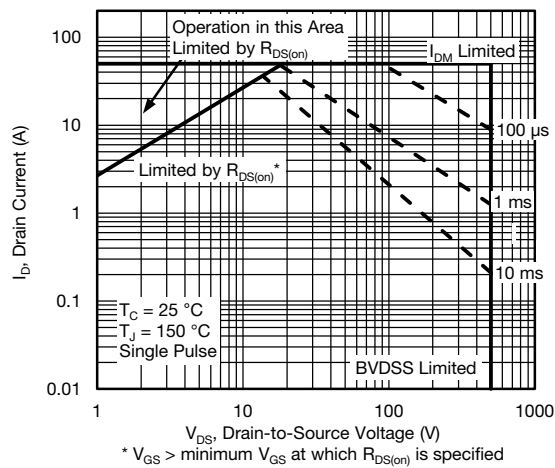


Fig. 9 - Maximum Safe Operating Area

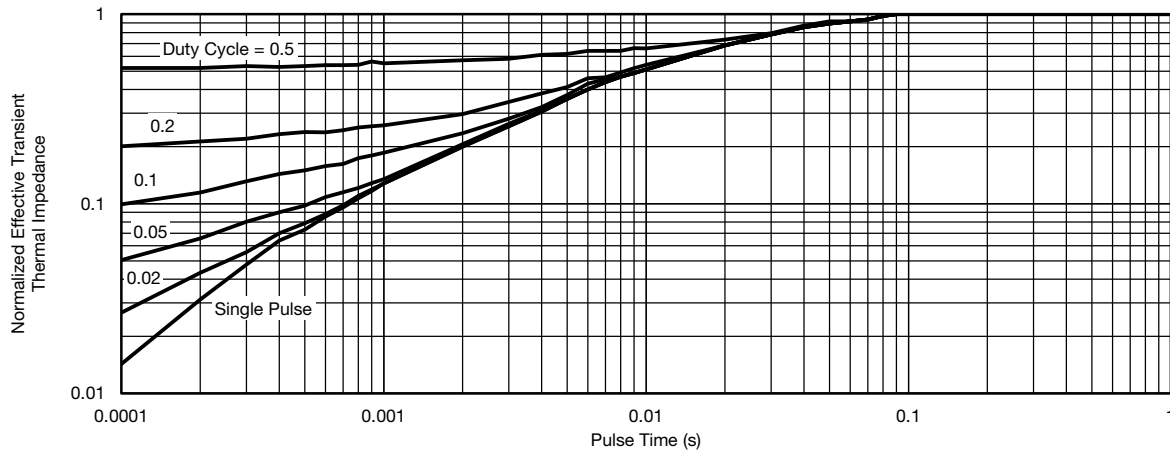


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

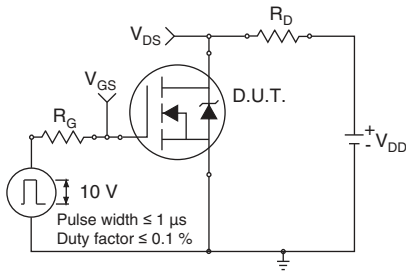


Fig. 13 - Switching Time Test Circuit

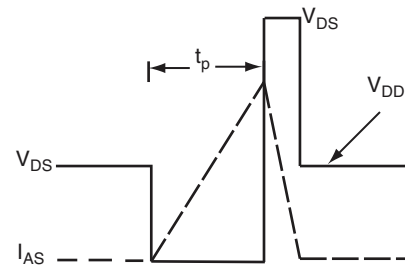


Fig. 16 - Unclamped Inductive Waveforms

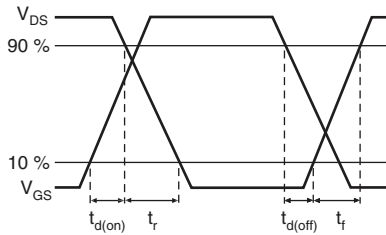


Fig. 14 - Switching Time Waveforms

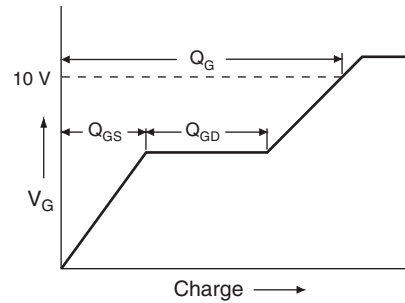


Fig. 17 - Basic Gate Charge Waveform

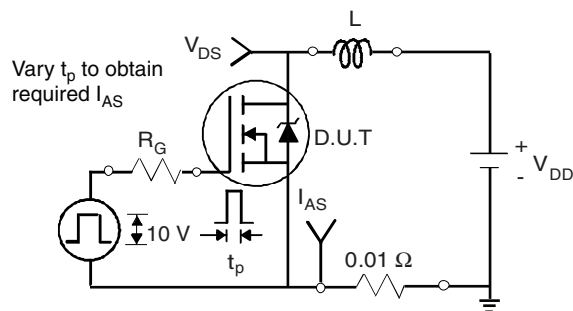


Fig. 15 - Unclamped Inductive Test Circuit

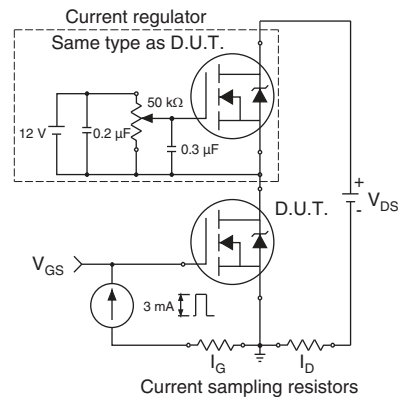
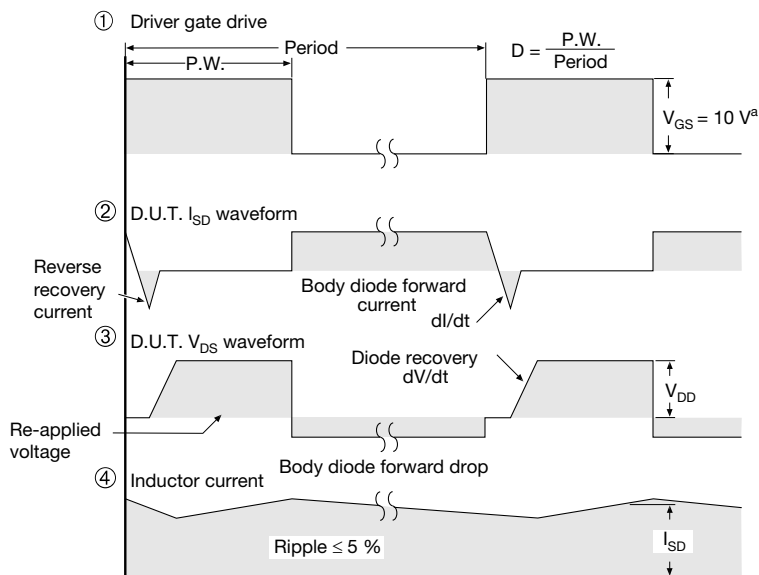
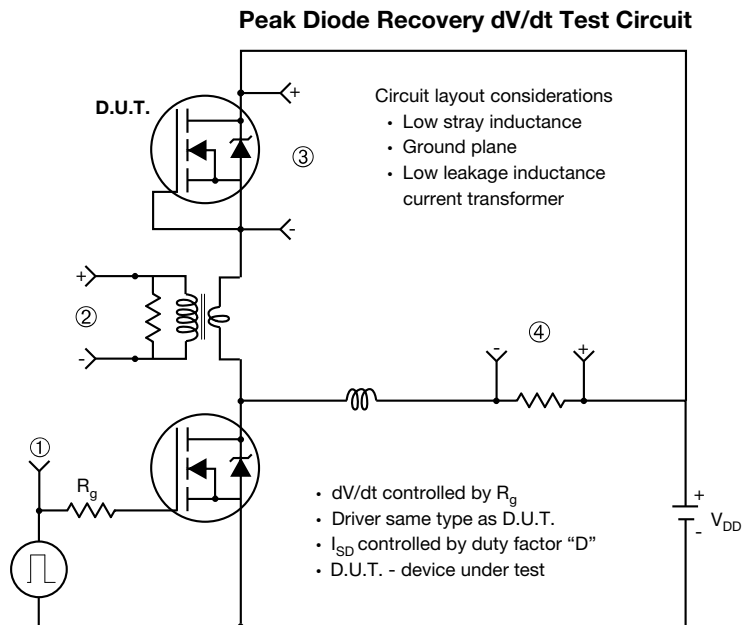


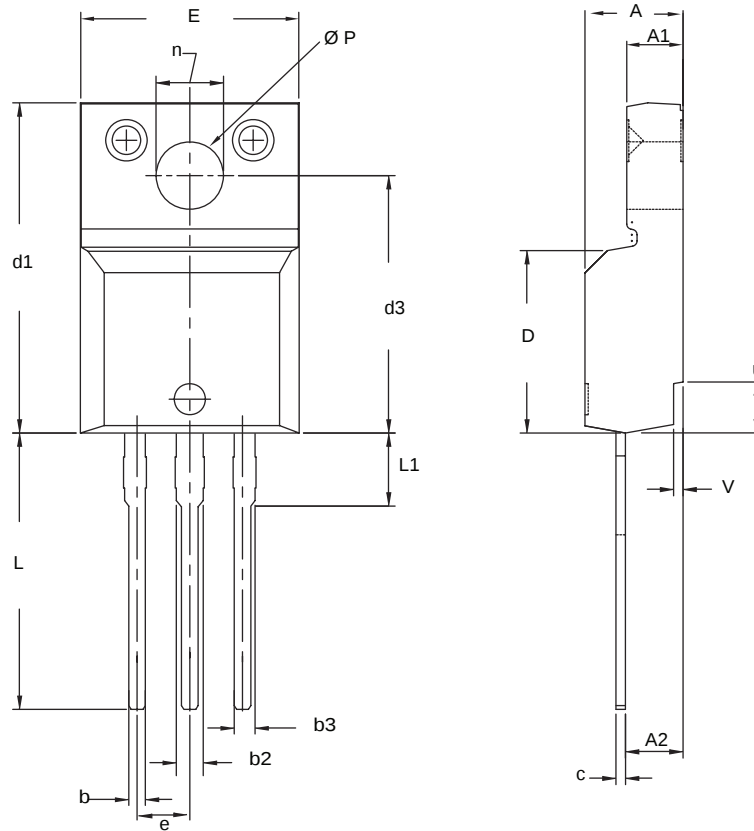
Fig. 18 - Gate Charge Test Circuit



**Note**

a.  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 19 - For N-Channel**

**TO-220 FULLPAK (HIGH VOLTAGE)**

| DIM. | MILLIMETERS |        | INCHES    |       |
|------|-------------|--------|-----------|-------|
|      | MIN.        | MAX.   | MIN.      | MAX.  |
| A    | 4.570       | 4.830  | 0.180     | 0.190 |
| A1   | 2.570       | 2.830  | 0.101     | 0.111 |
| A2   | 2.510       | 2.850  | 0.099     | 0.112 |
| b    | 0.622       | 0.890  | 0.024     | 0.035 |
| b2   | 1.229       | 1.400  | 0.048     | 0.055 |
| b3   | 1.229       | 1.400  | 0.048     | 0.055 |
| c    | 0.440       | 0.629  | 0.017     | 0.025 |
| D    | 8.650       | 9.800  | 0.341     | 0.386 |
| d1   | 15.88       | 16.120 | 0.622     | 0.635 |
| d3   | 12.300      | 12.920 | 0.484     | 0.509 |
| E    | 10.360      | 10.630 | 0.408     | 0.419 |
| e    | 2.54 BSC    |        | 0.100 BSC |       |
| L    | 13.200      | 13.730 | 0.520     | 0.541 |
| L1   | 3.100       | 3.500  | 0.122     | 0.138 |
| n    | 6.050       | 6.150  | 0.238     | 0.242 |
| Ø P  | 3.050       | 3.450  | 0.120     | 0.136 |
| u    | 2.400       | 2.500  | 0.094     | 0.098 |
| v    | 0.400       | 0.500  | 0.016     | 0.020 |

ECN: X09-0126-Rev. B, 26-Oct-09  
 DWG: 5972

**Notes**

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet  $C_{pk} > 1.33$ .
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.

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